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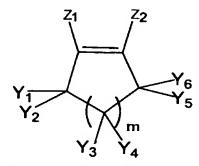
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## ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1, photoresist polymers thereof, and photoresist compositions containing the same. The photoresist polymers include a repeating unit comprising the photoresist monomer of Formula 1 as a comonomer and the photoresist compositions containing the same have excellent etching resistance, heat resistance and adhesiveness to a wafer, and are developable in aqueous tetramethylammonium hydroxide (TMAH) solutions. In addition, the photoresist compositions have a low light absorbance at 157nm wavelength, and thus are suitable for a photolithography process using ultraviolet light sources such as VUV (157nm) in fabricating a minute circuit for a high integration semiconductor device.

## Formula 1



wherein  $Y_1$ ,  $Y_2$ ,  $Y_3$ ,  $Y_4$ ,  $Y_5$ ,  $Y_6$ ,  $Z_1$ ,  $Z_2$  and m are defined in the specification.